## Single Driver for GaAs FET or PIN Diode Switches and Attenuators

## Features

- High Voltage CMOS Technology
- Complementary Outputs
- Positive Voltage Control
- CMOS device using TTL input levels
- Low Power Dissipation
- Low Cost Plastic SOIC-8 Package
- 100\% Matte Tin Plating over Copper
- Halogen-Free "Green" Mold Compound
- RoHS* Compliant


## Description

The MADR-009269 is a single channel CMOS driver used to translate TTL control inputs into complementary gate control voltages for GaAs FET microwave switches and attenuators. High speed analog CMOS technology is utilized to achieve low power dissipation at moderate to high speeds, encompassing most microwave switching applications. The output HIGH level is optionally 0 to 2 V (relative to GND) to optimize the intermodulation products of FET control devices at low frequencies. For driving PIN diode circuits, the outputs are nominally switched between +5 V \& -5 V .

## Ordering Information ${ }^{1}$

| Part Number | Package |
| :---: | :---: |
| MADR-009269-000100 | bulk packaging |
| MADR-009269-00GDIE | 100 piece gel pack |
| MADR-009269-000DIE | 100 piece waffle pack |
| MADR-009269-0001TR | 1000 piece reel |

1. Reference Application Note M513 for reel size information.

## Functional Schematic



Pin Configuration ${ }^{2}$

| Pin No. | Function |
| :---: | :---: |
| 1 | Output A |
| 2 | GND |
| 3 | $\mathrm{~V}_{\mathrm{CC}}$ |
| 4 | C, Logic |
| 5 | $\mathrm{~V}_{\mathrm{EE}}$ |
| 6 | $\mathrm{~V}_{\mathrm{OPT}}$ |
| 7 | GND |
| 8 | Output B |

2. The bottom of the die should be isolated for part number MADR-009269-000DIE and MADR-009269-00GDIE.
[^0]МАСОМ.

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## DC Characteristics over Guaranteed Operating Range

| Symbol | Parameter | Test Conditions | Units | Min. | Typ. | Max. |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| VIH | Input High Voltage | Guaranteed High Input Voltage | V | 2.0 | - | - |
| VIL | Input Low Voltage | Guaranteed Low Input Voltage | V | - | - | 0.8 |
| $\mathrm{V}_{\mathrm{OH}}$ | Output High Voltage | $\mathrm{I}_{\mathrm{OH}}=-1 \mathrm{~mA}$ | V | $V_{\text {OPT }}-0.1$ | - | - |
| $\mathrm{V}_{\text {OL }}$ | Output Low Voltage | $\mathrm{I}_{\mathrm{OL}}=+1 \mathrm{~mA}$ | V | - | - | $\mathrm{V}_{\mathrm{EE}}+0.1$ |
| $\mathrm{I}_{\mathrm{N}}$ | Input Leakage Current | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { or } \mathrm{GND}, \mathrm{~V}_{\mathrm{EE}}=\min , \\ & \mathrm{V}_{\mathrm{CC}}=\max , \mathrm{V}_{\mathrm{OPT}}=\min \text { or } \max \end{aligned}$ | $\mu \mathrm{A}$ | -1 | - | 1 |
| $\mathrm{R}_{\text {NFET }}$ | Output Resistance NFET On (to $V_{E E}$ ) | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}, \mathrm{~V}_{\mathrm{EE}}=-5.0 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{OPT}}=5.0 \mathrm{~V}, \mathrm{~V}_{\mathrm{OUT}}=-4.9 \mathrm{~V} \\ +25^{\circ} \mathrm{C} \end{gathered}$ | $\Omega$ | - | 30 | - |
| $\mathrm{R}_{\text {PFET }}$ | Output Resistance PFET On (to $\mathrm{V}_{\mathrm{OPT}}$ ) | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}, \mathrm{~V}_{\mathrm{EE}}=-5.0 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{OPT}}=5.0 \mathrm{~V}, \mathrm{~V}_{\mathrm{OUT}}=4.9 \mathrm{~V} \\ +25^{\circ} \mathrm{C} \end{gathered}$ | $\Omega$ | - | 30 | - |
| $\mathrm{I}_{\mathrm{cc}}$ | Quiescent Supply Current | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { or } \mathrm{GND}, \mathrm{~V}_{\mathrm{EE}}=-10.5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{OPT}}=5.5 \mathrm{~V}, \\ \text { No Output Load } \end{gathered}$ | $\mu \mathrm{A}$ | - | 1 | - |
| D I ${ }_{\text {cc }}$ | Additional Supply Current (per TTL Input pin) | $\mathrm{V}_{\mathrm{CC}}=\max , \mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {cc }}-2.1 \mathrm{~V}$ | mA | - | 1 | - |
| $\mathrm{I}_{\text {EE }}$ | Quiescent Supply Current | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { or } \mathrm{GND}, \mathrm{~V}_{\mathrm{EE}}=-10.5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{OPT}}=5.5 \mathrm{~V}, \\ \text { No Output Load } \end{gathered}$ | $\mu \mathrm{A}$ | - | 1 | - |
| $\mathrm{l}_{\text {OPT }}$ | Quiescent Supply Current | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { or } \mathrm{GND}, \mathrm{~V}_{\mathrm{EE}}=-10.5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{OPT}}=5.5 \mathrm{~V}, \\ \text { No Output Load } \end{gathered}$ | $\mu \mathrm{A}$ | - | 1 | - |

## AC Characteristics Over Guaranteed Operating Range ${ }^{3}$

| Symbol | Parameter | Unit | Typical performance |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | $-40^{\circ} \mathrm{C}$ | $+25^{\circ} \mathrm{C}$ | $+85^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {PLH }}$ | Propagation Delay | ns | 20 | 22 | 25 |
| $\mathrm{T}_{\text {PHL }}$ | Propagation Delay | ns | 20 | 22 | 25 |
| $\mathrm{T}_{\text {TLH }}$ | Output Transition Time (Rising Edge) | ns | 5 | 5 | 8 |
| $\mathrm{T}_{\text {THL }}$ | Output Transition Time (Falling Edge) | ns | 4 | 4 | 5 |
| $\mathrm{T}_{\text {skew }}$ | Delay Skew | ns | 2.5 | 2.5 | 2.5 |
| PRF (max) | 50\% Duty Cycle | MHz | DC | - | 10 |
| $\mathrm{C}_{\text {IN }}$ | Input Capacitance | pF | 5 | 5 | 5 |

3. $\mathrm{V}_{\mathrm{CC}}=+4.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{EE}}=-4.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{OPT}}=0 \mathrm{~V}$ or $+4.5 \mathrm{~V}, \mathrm{C}_{\mathrm{L}}=25 \mathrm{pF}, \mathrm{T}_{\mathrm{RISE}}, \mathrm{T}_{\text {FALL }}=6 \mathrm{~ns}$

## Truth Table

| Input | Outputs |  |
| :---: | :---: | :---: |
| C | $A$ | B |
| Logic "0" | $\mathrm{V}_{\mathrm{EE}}$ | $\mathrm{V}_{\mathrm{OPT}}$ |
| Logic "1" | $\mathrm{V}_{\mathrm{OPT}}$ | $\mathrm{V}_{\mathrm{EE}}$ |

## Handling Procedures

Please observe the following precautions to avoid damage:

## Static Sensitivity

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

## Guaranteed Operating Ranges ${ }^{4,5,6}$

| Symbol | Parameter | Unit | Min. | Typ. | Max. |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive DC Supply Voltage | V | 4.5 | 5.0 | 5.5 |
| $\mathrm{~V}_{\mathrm{EE}}$ | Negative DC Supply Voltage | V | -10.5 | -5.0 | -4.5 |
| $\mathrm{~V}_{\mathrm{OPT}}{ }^{7,8}$ | Optional DC Output Supply Voltage | V | 0 | - | $\mathrm{V}_{\mathrm{CC}}$ |
| $\mathrm{V}_{\mathrm{OPT}}-\mathrm{V}_{\mathrm{EE}}$ | Negative Supply Voltage Range | V | 4.5 | $\mathrm{Note} 7,8$ | 16.0 |
| $\mathrm{~V}_{\mathrm{CC}}-\mathrm{V}_{\mathrm{EE}}$ | Positive to negative Supply Range | V | 9 | 10 | 16 |
| $\mathrm{~T}_{\mathrm{OPER}}$ | Operating Temperature | ${ }^{\circ} \mathrm{C}$ | -40 | +25 | +85 |
| $\mathrm{I}_{\mathrm{OH}}$ | DC Output Current - High | mA | -50 | - | - |
| $\mathrm{I}_{\mathrm{OL}}$ | DC Output Current - Low | mA | - | - | 50 |
| $\mathrm{~T}_{\mathrm{RISE}} \mathrm{T}_{\mathrm{FALL}}$ | Maximum Input Rise or Fall Time | ns | - | - | 500 |

4. Unused logic inputs must be tied to either GND or $\mathrm{V}_{\mathrm{cc}}$.
5. MACOM recommends that $\mathrm{V}_{\mathrm{CC}}$ be powered on before $\mathrm{V}_{\mathrm{EE}}$, and powered off after $\mathrm{V}_{\mathrm{EE}}$.
6. $0.01 \mu \mathrm{~F}$ decoupling capacitors are required on the power supply lines.
7. $\mathrm{V}_{\text {OPT }}$ is grounded in most cases when FETs are driven. To improve the intermodulation performance and the 1 dB compression point of GaAs control devices at low frequencies, $\mathrm{V}_{\text {OPT }}$ can be increased to between 1 and 2 V . The nonlinear characteristics of the GaAs control devices will approximate performance at 500 MHz . It should be noted that the control current that is on the GaAs MMICs will increase when positive controls are applied.
8. When this driver is used to drive PIN diodes, $\mathrm{V}_{\mathrm{OPT}}$ is often set to +5 V , with $\mathrm{V}_{\text {EE }}$ set to -5 V .

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Absolute Maximum Ratings ${ }^{9}$

| Symbol | Parameter | Unit | Min. | Max. |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{cc}}$ | Positive DC Supply Voltage | V | -0.5 | 7.0 |
| Icc | Positive DC Supply Current ( $-0.5 \mathrm{~V} \leq \mathrm{V}_{\mathbb{I N}} \leq 0.8 \mathrm{~V}$; $\left.2.0 \mathrm{~V} \leq \mathrm{V}_{\mathrm{IN}} \leq \mathrm{V}_{\mathrm{CC}}+0.5 \mathrm{~V} ; \mathrm{V}_{\mathrm{CC}}-\mathrm{V}_{\mathrm{IN}} \leq 7.0 \mathrm{~V}\right)$ | mA | - | 20 |
| $V_{\text {EE }}$ | Negative DC Supply Voltage | V | -11.0 | 0.5 |
| $\mathrm{I}_{\text {EE }}$ | Negative DC Supply Current (per output) ${ }^{10}$ | mA | -60 | - |
| $V_{\text {OPT }}$ | Optional DC Output Supply Voltage | V | -0.5 | Note 11 |
| $\mathrm{I}_{\text {OPT }}$ | Optional DC Output Supply Current (per output) ${ }^{10}$ | mA | - | 60 |
| $\mathrm{V}_{\text {OPt }}-\mathrm{V}_{\text {EE }}$ | Output to Negative Supply Voltage Range | V | -0.5 | 18.0 |
| $\mathrm{V}_{\mathrm{CC}} . \mathrm{V}_{\mathrm{EE}}$ | Positive to Negative Supply Voltage Range | V | -0.5 | 18.0 |
| V IN | DC Input Voltage | V | $\begin{gathered} -0.5 \\ \text { Note } 12 \\ \hline \end{gathered}$ | $\mathrm{V}_{\mathrm{CC}}+0.5$ |
| $\mathrm{V}_{0}$ | DC Output Voltage | V | $V_{\text {EE }}-0.5$ | $\mathrm{V}_{\text {OPT }}+0.5$ |
| $\mathrm{P}_{\mathrm{D}}{ }^{13}$ | Power Dissipation in Still Air | mW | - | 500 |
| T OPER | Operating Temperature | ${ }^{\circ} \mathrm{C}$ | -55 | 125 |
| $\mathrm{T}_{\text {STG }}$ | Storage Temperature | ${ }^{\circ} \mathrm{C}$ | -65 | 150 |
| ESD | ESD Sensitivity | kV | 2.0 | - |

9. All voltages are referenced to GND. All inputs and outputs incorporate latch-up protection structures.
10. The maximum $\mathrm{I}_{\mathrm{EE}}$ and $\mathrm{I}_{\mathrm{OPT}}$ are specified under the condition of $\mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{EE}}=-5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{OPT}}=5.5 \mathrm{~V}$, and the total power dissipation is within 500 mW in still air.
11. The absolute maximum rating for $\mathrm{V}_{\mathrm{OPT}}$ is $\mathrm{V}_{\mathrm{CC}}+0.5 \mathrm{~V}$, or +7.0 V , whichever is less.
12. If $\mathrm{V}_{\mathrm{CC}} \geq 6.5 \mathrm{~V}$, then the minimum for $\mathrm{V}_{\mathrm{IN}}$ is $\mathrm{V}_{\mathrm{CC}}-7.0 \mathrm{~V}$.
13. Derate $-7 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$.

## Switching Waveforms



Equivalent Output Circuit for A and B Outputs ( 50 mA load at $25^{\circ} \mathrm{C}$ )


## Typical Application for a SPDT Switch



## Description of Circuit

The MADR-009269 provides a pair of complementary outputs that are each capable of driving a maximum of $\pm 50 \mathrm{~mA}$ into a load. In addition, with proper capacitor selection ( $\mathrm{C} 3 \& C 4$ ) used in parallel with the current setting resistor (R1 \& R2), additional spiking current can be achieved.

To achieve the non-inverting and inverting complementary voltages, each output is switched between two internal FETs. The FETs are connected to $V_{\text {OPT }}$ for the positive output and $V_{\text {EE }}$ for the negative output. $V_{\text {OPt }}$ and $\mathrm{V}_{\mathrm{EE}}$ are adjustable for various configurations and have the following limitations: $\mathrm{V}_{\mathrm{EE}}$ can be no more negative than -10.5 volts; $\mathrm{V}_{\text {OPT }}$ can be no more positive than +5.5 volts and $\mathrm{V}_{\text {OPT }}$ must always be less than or equal to $\mathrm{V}_{\mathrm{Cc}}$. Increasing $\mathrm{V}_{\text {OPT }}$ beyond $\mathrm{V}_{\mathrm{CC}}$ will prevent the device from switching states when commanded to by the logic input. The most common configuration is to drive $\mathrm{V}_{\mathrm{EE}}$ at -5.0 volts with $\mathrm{V}_{\mathrm{CC}}$ and $\mathrm{V}_{\mathrm{OPT}}$ tied together at +5.0 volts.

## Lead-Free, SOIC- $\mathbf{8}^{\dagger}$



[^1]
## Die Outline



Pad Configuration ${ }^{14,15}$
Die Size: $1130 \times 1290 \mu \mathrm{~m}$ (nominal)

| Pad <br> No. | $\mathbf{X}(\boldsymbol{\mu m})$ <br> nominal | $\mathbf{Y}(\boldsymbol{\mu m})$ <br> nominal | Pad Size $(\boldsymbol{\mu m})$ <br> $\mathbf{X} \mathbf{~ X ~ Y}$ |
| :---: | :---: | :---: | :---: |
| 0 | 0 | 0 | Lower left edge of die |
| 1 | 266.40 | 1092.35 | $94 \times 132$ |
| 2 | 157.50 | 903.70 | $85 \times 85$ |
| 3 | 200.40 | 663.65 | $85 \times 85$ |
| 4 | 365.30 | 200.45 | $85 \times 85$ |
| 5 | 684.35 | 157.50 | $85 \times 85$ |
| 6 | 972.50 | 230.50 | $85 \times 85$ |
| 7 | 972.50 | 451.45 | $85 \times 85$ |
| 8 | 863.60 | 1092.35 | $94 \times 132$ |
| 9 | 1130 | 1290 | Upper right edge of die |

14. All $X, Y$ dimensions are at bond pad center.
15. Die thickness is 8.0 mils.

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[^0]:    * Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.

[^1]:    ${ }^{\dagger}$ Reference Application Note M538 for lead-free solder reflow recommendations.
    Plating is $100 \%$ matte tin over copper.

